Digital Transistor (BRT) R1 = 1.0 k Ω , R2 = 10 k Ω

NPN Transistors with Monolithic Bias Resistor Network

This digital transistor is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector Current – Continuous	I _C	100	mAdc
Input Forward Voltage	V _{IN(fwd)}	30	Vdc
Input Reverse Voltage	V _{IN(rev)}	5	Vdc

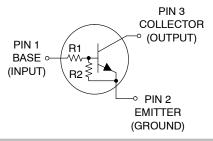
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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PIN CONNECTIONS



MARKING DIAGRAM



SOT-23 CASE 318 STYLE 6

AA6 = Specific Device Code

M = Date Code*

Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Table 1. ORDERING INFORMATION

Device	Package	Shipping [†]
MMUN2218LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

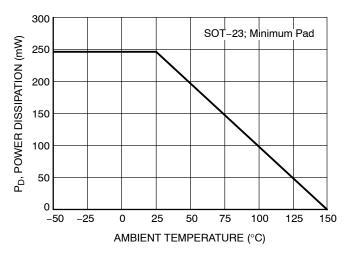


Figure 1. Derating Curve

Table 2. THERMAL CHARACTERISTICS

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-23)			•	•
Total Device Dissipation $T_A = 25^{\circ}C$	(Note 1) (Note 2)	P_{D}	246 400	mW
Derate above 25°C	(Note 1) (Note 2)		2.0 3.2	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	508 311	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	174 208	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C

^{1.} FR-4 @ Minimum Pad.

Table 3. ELECTRICAL CHARACTERISTICS (T_A = 25 $^{\circ}$ C, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Collector–Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	Ісво	-	_	100	nAdc	
Collector–Emitter Cutoff Current $(V_{CE} = 50 \text{ V}, I_B = 0)$	I _{CEO}	-	_	100	nAdc	
Emitter–Base Cutoff Current $(V_{EB} = 6.0 \text{ V}, I_C = 0)$	I _{EBO}	-	_	0.60	mAdc	
Collector–Base Breakdown Voltage ($I_C = 10 \mu A, I_E = 0$)	V _{(BR)CBO}	50	_	-	Vdc	
Collector-Emitter Breakdown Voltage (Note 3) (I _C = 2.0 mA, I _B = 0)	V _(BR) CEO	50	_	-	Vdc	
ON CHARACTERISTICS						
DC Current Gain (Note 5) (I _C = 5.0 mA, V _{CE} = 10 V)	h _{FE}	40	60	_		
Collector – Emitter Saturation Voltage (Note 3) (I _C = 10 mA, I _B = 1.0 mA)	VCE(sat)	-	_	0.25	Vdc	
Input Voltage (off) (V _{CE} = 5.0 V, I _C = 100 μ A)	V _{i(off)}	-	0.7	0.5	Vdc	
Input Voltage (on) ($V_{CE} = 0.3 \text{ V}, I_{C} = 5 \text{ mA}$)	V _{i(on)}	1.3	0.9	_	Vdc	
Output Voltage (on) ($V_{CC} = 5.0 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1.0 \text{ k}\Omega$)	V _{OL}	-	-	0.2	Vdc	
Output Voltage (off) (V _{CC} = 5.0 V, V _B = 0.5 V, R _L = 1.0 k Ω)	V _{OH}	4.9	_	-	Vdc	
Input Resistor	R1	0.7	1.0	1.3	kΩ	
Resistor Ratio	R ₁ /R ₂	0.08	0.1	0.12		

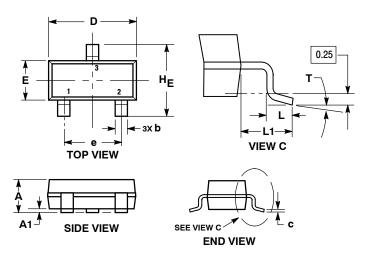
^{3.} Pulsed Condition: Pulse Width = 300 msec, Duty Cycle \leq 2%.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{2.} FR-4 @ 1.0 x 1.0 Inch Pad.

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AR**



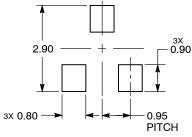
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS.

	М	ILLIMETE	RS	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.89	1.00	1.11	0.035	0.039	0.044	
A1	0.01	0.06	0.10	0.000	0.002	0.004	
b	0.37	0.44	0.50	0.015	0.017	0.020	
С	0.08	0.14	0.20	0.003	0.006	0.008	
D	2.80	2.90	3.04	0.110	0.114	0.120	
E	1.20	1.30	1.40	0.047	0.051	0.055	
е	1.78	1.90	2.04	0.070	0.075	0.080	
L	0.30	0.43	0.55	0.012	0.017	0.022	
L1	0.35	0.54	0.69	0.014	0.021	0.027	
HE	2.10	2.40	2.64	0.083	0.094	0.104	
Т	0°		10 °	0 °		10 °	

STYLE 6:

- PIN 1. BASE
 - **EMITTER**
 - 2. 3. COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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